<u>SENSITRON</u> SEMICONDUCTOR

TECHNICAL DATA DATA SHEET 1006, REV. -Formerly part number –SHSMG1009

600 VOLT, 40 AMP IGBT DEVICE HIGH SPEED, IMPROVED SCSOA

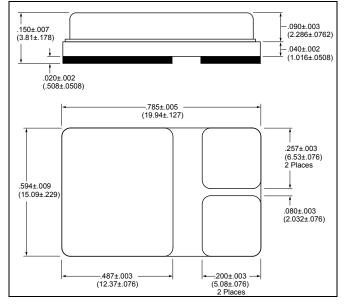
ELECTRICAL CHARACTERISTICS	(Tj=25 ⁰ C UNLESS OTHERWISE SPECIFIED)				
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
IGBT SPECIFICATIONS					
Collector to Emitter Breakdown Voltage	BV _{CES}	600	-	-	V
I _C = 250 μA, V _{GE} = 0V					
Continuous Collector Current $T_{C} = 25 \ ^{\circ}C$ $T_{C} = 90 \ ^{\circ}C$	Ic	-	-	40 ⁽¹⁾ 40	А
Pulsed Collector Current, 1mS	I _{CM}	-	-	130	А
Short Circuit time, V_{GE} = 15V, V_{CE} = 500V, T_j = 125 $^{\circ}C$ di/dt < 300 A/ sec, I_C < 300A	t _{sc}	-	-	10	sec
Gate to Emitter Voltage	V _{GE}	-	-	+/-20	V
Gate-Emitter Leakage Current, V _{GE} = +/-20V	I _{GES}	-	-	+/- 100	nA
Gate Threshold Voltage, I_{C} =2mA	V _{GE(TH)}	4.0	-	7.0	V
Zero Gate Voltage Collector Current $V_{CE} = 600 \text{ V}, V_{GE} = 0 \text{ V} T_i = 25^{\circ} \text{ C}$	I _{CES}	_	_	0.25	Ма
$V_{CE} = 480 \text{ V}, V_{GE} = 0 \text{ V} T_i = 125^{\circ} \text{C}$		-	-	3.0	mA
Collector to Emitter Saturation Voltage, $T_c = 25 ^{\circ}C$ $I_c = 40A, V_{GE} = 15V,$ $T_c = 125 ^{\circ}C$	V _{CE(SAT)}	-	2.0 2.3	2.3 2.5	V
Input Capacitance Output Capacitance Reverse Transfer Cap. $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	C _{ies} C _{oes} C _{res}	-	2800 300 200	-	pF
Turn On Delay Time	t _{d(on)}	-	100	-	
Rise Time Turn Off Delay Time	t _r t _{d(off)}	-	50 300	-	nsec
Fall Time	t _f	-	40	-	
Turn off Energy Loss	-		4 5		
$(T_j = 125 {}^{\circ}C, I_C = 40A, V_{GE} = 15V, inductive load, V_{CC} = 220 V D = 220 C$	E _{off}	-	1.5	-	mJ
300 V, R _G = 22 Ω	E _{on}	-	2.0	-	mJ
Maximum Thermal Resistance	$R_{ ext{ heta}JC}$	-	-	0.60	°C/W

(1) Current is limited by package leads. Die current rating is 65A.

(2) Current is limited by package leads. Die current rating is 75A.

(3) Current is limited by package leads. Die current rating is 50A.

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Mechanical Dimensions: In Inches / mm



Schematic Diagram



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